

2SB1132 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.5 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

$$I_{CM}: -1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -40 \text{ V}$$

Operating and storage junction temperature range

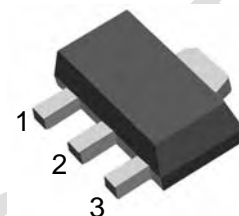
$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-0.5	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -3\text{V}, I_C = -100\text{mA}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -50\text{mA}, f = 30\text{MHz}$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		20	30	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BAP	BAQ	BAR